

Abstract

The present application relates to a semiconductor electrostatic protection device, including: a substrate, a deep well region of a first conductivity type being formed in the substrate; a first diode, an anode of the first diode being connected to a first voltage, and a cathode of the first diode being connected to an input/output terminal; and a second diode, an anode of the second diode being connected to the input/output terminal, and a cathode of the second diode being connected to a second voltage; the first diode and the second diode being located in the deep well region of the first conductivity type.